

BD243/A/B/C

Medium Power Linear and Switching Applications

Complement to BD244, BD244A, BD244B and BD244C respectively



1.Base 2.Collector 3.Emitter

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage		
	: BD243	45	V
	: BD243A	60	V
	: BD243B	80	V
	: BD243C	100	V
V _{CEO}	Collector-Emitter Voltage		
	: BD243	45	V
	: BD243A	60	V
	: BD243B	80	V
	: BD243C	100	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current (DC)	6	А
I _{CP}	*Collector Current (Pulse)	10	А
I _B	Base Current	2	А
P _C	Collector Dissipation (T _C =25°C)	65	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 65 ~ 150	°C

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V _{CEO} (sus)	* Collector-Emitter Sustaining Voltage		144		-71	
	: BD243	$I_C=30$ mA, $I_B=0$	45			V
	: BD243A	- 1 to 10 to	60	Take N	Thr.	V
	: BD243B	Jan Litt 1	80	A. A		V
	: BD243C		100			V
I _{CEO}	Collector Cut-off Current : BD243/243A	$V_{CE} = 30V, I_{B} = 0$			0.7	mA
	: BD243B/243C	$V_{CE} = 60V, I_{B} = 0$			0.7	mA
I _{CES}	Collector Cut-off Current : BD243	$V_{CE} = 45V, V_{BE} = 0$			0.4	mA
	: BD243A	$V_{CE} = 60V, V_{BE} = 0$			0.4	mA
	: BD243B	$V_{CE} = 80V, V_{BE} = 0$			0.4	mA
	: BD243C	$V_{CE} = 100V, V_{BE} = 0$			0.4	mA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			1	mA
h _{FE}	*DC Current Gain	$V_{CE} = 4V, I_{C} = 0.3A$	30			
		$V_{CE} = 4V, I_{C} = 3A$	15			
V _{CE} (sat)	*Collector-Emitter Saturation Voltage	$I_C = 6A, I_B = 1A$			1.5	V
V _{BE} (on)	*Base-Emitter ON Voltage	$V_{CE} = 4V, I_{C} = 6A$			2	V

Pulse Test :PW=300μs, duty Cycle<20% Pulsed

Typical Characteristics

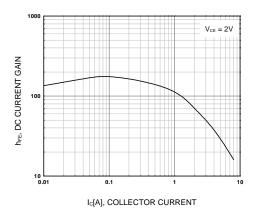


Figure 1. DC current Gain

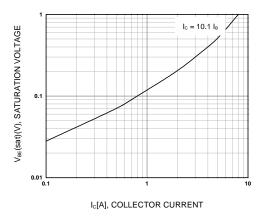


Figure 3. Collector-Emitter Saturation Voltage

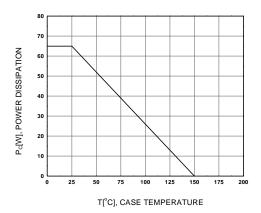


Figure 5. Power Derating

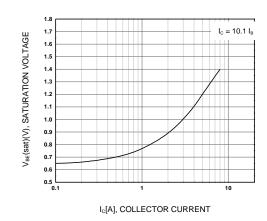
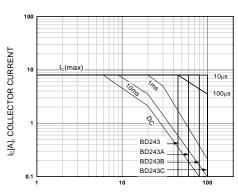


Figure 2. Base-Emitter Saturation Voltage



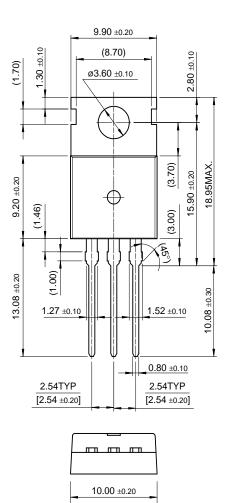
 $V_{CE}[V]$, COLLECTOR-EMITTER VOLTAGE

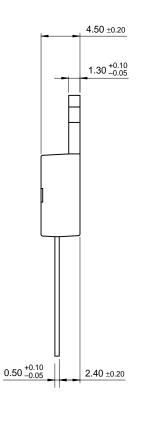
Figure 4. Safe Operating Area

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Package Demensions

TO-220





Dimensions in Millimeters

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